Docket Number (Optional)	Application Number
51889/2	10/613,169
Applicant(s)	
Douglas R. Hackler, Sr. et al.	
Filing Date	**Group Art Unit**
July 3, 2003	2811

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
PC	A1	2003/0058001	03/27/03	Boerstler et al.	326	113	09/27/01
	A2	2002/0180486	12/05/02	Yamashita et al.	326	113	06/25/02
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Sheet 1 of 7

FORM PTO-1449 (REV. 7-80)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 51889/2 US	APPLICATION NO. 10/613,169
INFORMATION DISCLOSURE CITATION		APPLICANT – Douglas R. Hackler, Sr. et al.	
Title: **MULTI-CONFIGURABLE INDEPENDENTLY MULTI-GATED MOSFET**		FILING DATE- July 3, 2003	

U.S. PATENT DOCUMENTS

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